

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|---|------------------|
| - | 4809 | ((438/149-154) or (257/347-352) or (257/59,72) or (348/46)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 09:49 |
| - | 7 | ((("5698869") or ("5728592"))).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/06 16:24 |
| - | 71 | ((("438/149-154") or ("257/347-352") or ("257/59,72") or ("348/46")).CCLS.) and ((anodizing or anodically or anodized) near (oxide or oxygen or oxidized)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/07 09:34 |
| - | 266 | ((thin adj film adj transistor) or TFT) and ((anodically or anodizing or anode) near (oxidized or oxidizing or oxidized)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/07 09:55 |
| - | 29 | ((thin adj film adj transistor) or TFT) and ((anodically or anodizing or anode) near (oxidized or oxidizing or oxidized))) and (angled or tapered or tapered) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/07 09:57 |
| - | 396 | ((photoresist or resist or (photo adj resist)) near (bake or baked)) same temperature | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/07 12:10 |
| - | 9 | ((photoresist or resist or (photo adj resist)) near (bake or baked)) same temperature) and (TFT or (thin adj film adj transistor)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/07 12:11 |
| - | 586 | anodically adj oxidizing | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/07 13:29 |
| - | 1 | ("5202274").PN. | USPAT | 2002/03/07 13:00 |
| - | 20 | 5202274.URPN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/07 13:02 |
| - | 0 | (anodically adj oxidizing) near (advantage or advantages) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/07 13:30 |
| - | 4 | (anodically adj oxidizing) same (advantage or advantages) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/03/07 13:30 |
| - | 0 | ((anodic or anodical) near (oxidiz\$3)) same (Al or aluminum)) and ((native near oxide) same (etch or etched or etching)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 09:52 |
| - | 1562 | (Al or aluminum) and ((native near oxide) same (etch or etched or etching)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 09:52 |
| - | 326 | (Al or aluminum) same ((native near oxide) same (etch or etched or etching)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 09:52 |

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| - | 0 | (Al or aluminum) same ((native near oxide) same (etch or etched or etching)) and (anodically near oxidizing) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 09:53 |
| - | 286 | (Al or aluminum) same ((native near oxide) same (etch or etched or etching)) and (semiconductor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 09:54 |
| - | 252 | (Al or aluminum) same ((native near oxide) same (etch or etched or etching)) and (semiconductor) | USPAT; DERWENT; IBM_TDB | 2003/04/15 09:55 |
| - | 20 | (plasma near chamber) same (cooling near medium) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 14:09 |
| - | 18 | (plasma near chamber) same (cooling near medium) | USPAT; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 14:12 |
| - | 82 | (plasma near chamber) same (cool\$4 with substrate) | USPAT; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 15:04 |
| - | 306 | antifuse with oxide | USPAT; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 15:04 |
| - | 240 | (antifuse with oxide) and semiconductor | USPAT; EPO; JPO; DERWENT; IBM_TDB | 2003/04/15 15:04 |
| - | 175 | ((438/466).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/11 09:25 |
| - | 24 | ((438/466).CCLS.) and anodic\$4 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/11 10:51 |
| - | 13 | ((438/466).CCLS.) and anodic\$4 and (thin near (film or layer)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/11/11 10:51 |